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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

E·XFI

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-fg256

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

FPGA Array Architecture in Low Power Flash Devices



Note: Flash*Freeze technology only applies to IGLOOe devices.

Figure 1-7 • IGLOOe and ProASIC3E Device Architecture Overview (AGLE600 device is shown)

I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

Global Resources in Low Power Flash Devices

Global Resource Support in Flash-Based Devices

The flash FPGAs listed in Table 3-1 support the global resources and the functions described in this document.

Table 3-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO products as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Implementing EXTFB in ProASIC3/E Devices

When the external feedback (EXTFB) signal of the PLL in the ProASIC3/E devices is implemented, the phase detector of the PLL core receives the reference clock (CLKA) and EXTFB as inputs. EXTFB must be sourced as an INBUF macro and located at the global/chip clock location associated with the target PLL by Designer software. EXTFB cannot be sourced from the FPGA fabric.

The following example shows CLKA and EXTFB signals assigned to two global I/Os in the same global area of ProASIC3E device.





Config. Bits	Signal	Name	Description
83	RXCSEL ¹	CLKC input selection	Select the CLKC input clock source between RC oscillator and crystal oscillator (refer to Table 4-16 on page 110). ²
82	RXBSEL ¹	CLKB input selection	Select the CLKB input clock source between RC oscillator and crystal oscillator (refer to Table 4-16 on page 110). ²
81	RXASEL ¹	CLKA input selection	Select the CLKA input clock source between RC oscillator and crystal oscillator (refer to Table 4-16 on page 110). ²
80	RESETEN	Reset Enable	Enables (active high) the synchronization of PLL output dividers after dynamic reconfiguration (SUPDATE). The Reset Enable signal is READ-ONLY.
79	DYNCSEL	Clock Input C Dynamic Select	Configures clock input C to be sent to GLC for dynamic control. ²
78	DYNBSEL	Clock Input B Dynamic Select	Configures clock input B to be sent to GLB for dynamic control. ²
77	DYNASEL	Clock Input A Dynamic Select	Configures clock input A for dynamic PLL configuration. ²
<76:74>	VCOSEL[2:0]	VCO Gear Control	Three-bit VCO Gear Control for four frequency ranges (refer to Table 4-19 on page 111 and Table 4-20 on page 111).
73	STATCSEL	MUX Select on Input C	MUX selection for clock input C ²
72	STATBSEL	MUX Select on Input B	MUX selection for clock input B ²
71	STATASEL	MUX Select on Input A	MUX selection for clock input A ²
<70:66>	DLYC[4:0]	YC Output Delay	Sets the output delay value for YC.
<65:61>	DLYB[4:0]	YB Output Delay	Sets the output delay value for YB.
<60:56>	DLYGLC[4:0]	GLC Output Delay	Sets the output delay value for GLC.
<55:51>	DLYGLB[4:0]	GLB Output Delay	Sets the output delay value for GLB.
<50:46>	DLYGLA[4:0]	Primary Output Delay	Primary GLA output delay
45	XDLYSEL	System Delay Select	When selected, inserts System Delay in the feedback path in Figure 4-20 on page 101.
<44:40>	FBDLY[4:0]	Feedback Delay	Sets the feedback delay value for the feedback element in Figure 4-20 on page 101.
<39:38>	FBSEL[1:0]	Primary Feedback Delay Select	Controls the feedback MUX: no delay, include programmable delay element, or use external feedback.
<37:35>	OCMUX[2:0]	Secondary 2 Output Select	Selects from the VCO's four phase outputs for GLC/YC.
<34:32>	OBMUX[2:0]	Secondary 1 Output Select	Selects from the VCO's four phase outputs for GLB/YB.

Table 4-8 • Configuration Bit Descriptions for the CCC Blocks (continued)

Notes:

1. The <88:81> configuration bits are only for the Fusion dynamic CCC.

 This value depends on the input clock source, so Layout must complete before these bits can be set. After completing Layout in Designer, generate the "CCC_Configuration" report by choosing Tools > Report > CCC_Configuration. The report contains the appropriate settings for these bits.

FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

- Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
- Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
- 3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, Load Sim. Value From File allows you to load the first device data in the MEM file for simulation.
- 4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 • SmartGen GUI of the FlashROM

SRAM Features

RAM4K9 Macro

RAM4K9 is the dual-port configuration of the RAM block (Figure 6-4). The RAM4K9 nomenclature refers to both the deepest possible configuration and the widest possible configuration the dual-port RAM block can assume, and does not denote a possible memory aspect ratio. The RAM block can be configured to the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, and 512×9. RAM4K9 is fully synchronous and has the following features:

- Two ports that allow fully independent reads and writes at different frequencies
- Selectable pipelined or nonpipelined read
- Active-low block enables for each port
- Toggle control between read and write mode for each port
- · Active-low asynchronous reset
- Pass-through write data or hold existing data on output. In pass-through mode, the data written to the write port will immediately appear on the read port.
- Designer software will automatically facilitate falling-edge clocks by bubble-pushing the inversion to previous stages.



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet. *Figure 6-4* • RAM4K9 Simplified Configuration

Signal Descriptions for RAM4K9

Note: Automotive ProASIC3 devices support single-port SRAM capabilities, or dual-port SRAM only under specific conditions. Dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). Since Libero SoC macro libraries support a dual-port macro only, certain modifications must be made. These are detailed below.

The following signals are used to configure the RAM4K9 memory element:

WIDTHA and WIDTHB

These signals enable the RAM to be configured in one of four allowable aspect ratios (Table 6-2 on page 154).

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WIDTHB should be tied to ground.

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet.

Figure 6-5 • 512X18 Two-Port RAM Block Diagram

Signal Descriptions for RAM512X18

RAM512X18 has slightly different behavior from RAM4K9, as it has dedicated read and write ports.

WW and RW

These signals enable the RAM to be configured in one of the two allowable aspect ratios (Table 6-5).

WW[1:0]	RW[1:0]	D×W
01	01	512×9
10	10	256×18
00, 11	00, 11	Reserved

WD and RD

These are the input and output data signals, and they are 18 bits wide. When a 512×9 aspect ratio is used for write, WD[17:9] are unused and must be grounded. If this aspect ratio is used for read, RD[17:9] are undefined.

WADDR and RADDR

These are read and write addresses, and they are nine bits wide. When the 256×18 aspect ratio is used for write or read, WADDR[8] and RADDR[8] are unused and must be grounded.

WCLK and RCLK

These signals are the write and read clocks, respectively. They can be clocked on the rising or falling edge of WCLK and RCLK.

WEN and REN

These signals are the write and read enables, respectively. They are both active-low by default. These signals can be configured as active-high.

RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

PIPE

This signal is used to specify pipelined read on the output. A LOW on PIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

Table 7-8 • Hot-Swap Level 1

Description	Cold-swap
Power Applied to Device	No
Bus State	-
Card Ground Connection	-
Device Circuitry Connected to Bus Pins	-
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices: Compliant Other IGLOO/ProASIC3 devices: Compliant if bus switch used to isolate FPGA I/Os from rest of system IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode.

Table 7-9 • Hot-Swap Level 2

Description	Hot-swap while reset		
Power Applied to Device	Yes		
Bus State	Held in reset state		
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.		
Device Circuitry Connected to Bus Pins	-		
Example Application	In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.		
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode. Other IGLOO/ProASIC3 devices: Compliant		

I/O Structures in IGLOOe and ProASIC3E Devices

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) refers to bus interface circuits based on LVDS technology. Multipoint LVDS (M-LVDS) specifications extend the LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The driver requires series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus, since the driver can be located anywhere on the bus. These configurations can be implemented using TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 8-9. The input and output buffer delays are available in the LVDS sections in the datasheet.

Example: For a bus consisting of 20 equidistant loads, the terminations given in EQ 8-1 provide the required differential voltage, in worst case industrial operating conditions, at the farthest receiver:

 $R_S = 60 \Omega$, $R_T = 70 \Omega$, given $Z_O = 50 \Omega$ (2") and $Z_{stub} = 50 \Omega$ (~1.5").



Figure 8-9 • A B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers

Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout

Each I/O voltage bank has a separate ground and power plane for input and output circuits (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa.

Since voltage bounce originates on the package inductance, the VMV and VCCI supplies have separate package pin assignments. For the same reason, GND and GNDQ also have separate pin assignments.

The VMV and VCCI pins must be shorted to each other on the board. Also, the GND and GNDQ pins must be shorted to each other on the board. This will prevent unwanted current draw from the power supply.

SSOs can cause signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities (EQ 8-2 and EQ 8-3).

Ground bounce noise voltage = $L(GND) \times di/dt$

VCCI dip noise voltage = $L(VCCI) \times di/dt$

EQ 8-3

EQ 8-2

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to the SSO bus are LVTTL/LVCMOS inputs, LVTTL/LVCMOS outputs, or GTL/SSTL/HSTL/LVDS/LVPECL inputs and outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to be considered are as follows:

- Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

For extensive data per package on the SSO and PCB issues, refer to the "ProASIC3/E SSO and Pin Placement and Guidelines" chapter of the *ProASIC3 FPGA Fabric User's Guide*.

I/O Structures in IGLOOe and ProASIC3E Devices

Table 8-18 • Supported IGLOOe, ProASIC3L, and ProASIC3E I/O Standards and Corresponding VREF and VTT Voltages

I/O Standard	Input/Output Supply Voltage (VMV _{TYP} /V _{CCI_TYP})	Input Reference Voltage (V _{REF_TYP})	Board Termination Voltage (V _{TT_TYP})
LVTTL/ L VCMOS 3.3 V	3.30 V	-	-
LVCMOS 2.5 V	2.50 V	-	_
LVCMOS 2.5/5.0 V Input	2.50 V	-	-
LVCMOS 1.8 V	1.80 V	-	-
LVCMOS 1.5 V	1.50 V	-	_
PCI 3.3 V	3.30 V	-	-
PCI-X 3.3 V	3.30 V	-	-
GTL+ 3.3 V	3.30 V	1.00 V	1.50 V
GTL+ 2.5 V	2.50 V	1.00 V	1.50 V
GTL 3.3 V	3.30 V	0.80 V	1.20 V
GTL 2.5 V	2.50 V	0.80 V	1.20 V
HSTL Class I	1.50 V	0.75 V	0.75 V
HSTL Class II	1.50 V	0.75 V	0.75 V
SSTL3 Class I	3.30 V	1.50 V	1.50 V
SSTL3 Class II	3.30 V	1.50 V	1.50 V
SSTL2 Class I	2.50 V	1.25 V	1.25 V
SSTL2 Class II	2.50 V	1.25 V	1.25 V
LVDS, DDR LVDS, B-LVDS, M-LVDS	2.50 V	-	-
LVPECL	3.30 V	-	-

I/O Bank Resource Usage

This is an important portion of the report. The user must meet the requirements stated in this table. Figure 9-10 shows the I/O Bank Resource Usage table included in the I/O bank report:

Figure 9-10 • I/O Bank Resource Usage Table

The example in Figure 9-10 shows that none of the I/O macros is assigned to the bank because more than one VCCI is detected.

I/O Voltage Usage

The I/O Voltage Usage table provides the number of VREF (E devices only) and V_{CCI} assignments required in the design. If the user decides to make I/O assignments manually (PDC or MVN), the issues listed in this table must be resolved before proceeding to Layout. As stated earlier, VREF assignments must be made if there are any voltage-referenced I/Os.

Figure 9-11 shows the I/O Voltage Usage table included in the I/O bank report.

Figure 9-11 • I/O Voltage Usage Table

The table in Figure 9-11 indicates that there are two voltage-referenced I/Os used in the design. Even though both of the voltage-referenced I/O technologies have the same VCCI voltage, their VREF voltages are different. As a result, two I/O banks are needed to assign the VCCI and VREF voltages.

In addition, there are six single-ended I/Os used that have the same VCCI voltage. Since two banks are already assigned with the same VCCI voltage and there are enough unused bonded I/Os in



DDR for Microsemi's Low Power Flash Devices

Table 10-2 • DDR I/O Options (continued)

DDR Register	I/O Type	I/O Standard	Sub-Ontions	Comments	
Transmit Register	Tristate	Normal	Enable Polarity	Low/bigb (low default)	
(continued)	Buffer	LVTTL	Output Drive	2, 4, 6, 8, 12,16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)	
			Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		PCI/PCI-X	Enable Polarity	Low/high (low default)	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)	
			Enable Polarity	Low/high (low default)	
		HSTL	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
		SSTL2/SSTL3	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
	Bidirectional Buffer	Normal	Enable Polarity	Low/high (low default)	
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up	None (default)	
		PCI/PCI-X	None		
			Enable Polarity	Low/high (low default)	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)	
			Enable Polarity	Low/high (low default)	
		HSTL	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
		SSTL2/SSTL3	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	

Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.



Types of Programming for Flash Devices

The number of devices to be programmed will influence the optimal programming methodology. Those available are listed below:

- In-system programming
 - Using a programmer
 - Using a microprocessor or microcontroller
- Device programmers
 - Single-site programmers
 - Multi-site programmers, batch programmers, or gang programmers
 - Automated production (robotic) programmers
- Volume programming services
 - Microsemi in-house programming
 - Programming centers

In-System Programming

Device Type Supported: Flash

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ISP refers to programming the FPGA after it has been mounted on the system printed circuit board. The FPGA may be preprogrammed and later reprogrammed using ISP.

The advantage of using ISP is the ability to update the FPGA design many times without any changes to the board. This eliminates the requirement of using a socket for the FPGA, saving cost and improving reliability. It also reduces programming hardware expenses, as the ISP methodology is die-/package-independent.

There are two methods of in-system programming: external and internal.

Programmer ISP—Refer to the "In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" section on page 327 for more information.

Using an external programmer and a cable, the device can be programmed through a header on the system board. In Microsemi SoC Products Group documentation, this is referred to as external ISP. Microsemi provides FlashPro4, FlashPro3, FlashPro Lite, or Silicon Sculptor 3 to perform external ISP. Note that Silicon Sculptor II and Silicon Sculptor 3 can only provide ISP for ProASIC and ProASIC^{PLUS®} families, not for SmartFusion, Fusion, IGLOO, or ProASIC3. Silicon Sculptor II and Silicon Sculptor 3 can be used for programming ProASIC and ProASIC^{PLUS®} devices by using an adapter module (part number SMPA-ISP-ACTEL-3).

- Advantages: Allows local control of programming and data files for maximum security. The programming algorithms and hardware are available from Microsemi. The only hardware required on the board is a programming header.
- Limitations: A negligible board space requirement for the programming header and JTAG signal routing
- Microprocessor ISP—Refer to the "Microprocessor Programming of Microsemi's Low Power Flash Devices" chapter of an appropriate FPGA fabric user's guide for more information.

Using a microprocessor and an external or internal memory, you can store the program in memory and use the microprocessor to perform the programming. In Microsemi documentation, this is referred to as internal ISP. Both the code for the programming algorithm and the FPGA programming file must be stored in memory on the board. Programming voltages must also be generated on the board.

- Advantages: The programming code is stored in the system memory. An external programmer is not required during programming.
- Limitations: This is the approach that requires the most design work, since some way of getting and/or storing the data is needed; a system interface to the device must be designed; and the low-level API to the programming firmware must be written and linked into the code provided by Microsemi. While there are benefits to this methodology, serious thought and planning should go into the decision.

Programming Solutions

Details for the available programmers can be found in the programmer user's guides listed in the "Related Documents" section on page 297.

All the programmers except FlashPro4, FlashPro3, FlashPro Lite, and FlashPro require adapter modules, which are designed to support device packages. All modules are listed on the Microsemi SoC Products Group website at

http://www.microsemi.com/soc/products/hardware/program_debug/ss/modules.aspx. They are not listed in this document, since this list is updated frequently with new package options and any upgrades required to improve programming yield or support new families.

Programmer	Vendor	ISP	Single Device	Multi-Device	Availability
FlashPro4	Microsemi	Only	Yes	Yes ¹	Available
FlashPro3	Microsemi	Only	Yes	Yes ¹	Available
FlashPro Lite ²	Microsemi	Only	Yes	Yes ¹	Available
FlashPro	Microsemi	Only	Yes	Yes ¹	Discontinued
Silicon Sculptor 3	Microsemi	Yes ³	Yes	Cascade option (up to two)	Available
Silicon Sculptor II	Microsemi	Yes ³	Yes	Cascade option (up to two)	Available
Silicon Sculptor	Microsemi	Yes	Yes	Cascade option (up to four)	Discontinued
Sculptor 6X	Microsemi	No	Yes	Yes	Discontinued
BP MicroProgrammers	BP Microsystems	No	Yes	Yes	Contact BP Microsystems at www.bpmicro.com

Table 11-3 • Programming Solutions

Notes:

1. Multiple devices can be connected in the same JTAG chain for programming.

2. If FlashPro Lite is used for programming, the programmer derives all of its power from the target pc board's VDD supply. The FlashPro Lite's VPP and VPN power supplies use the target pc board's VDD as a power source. The target pc board must supply power to both the VDDP and VDD power pins of the ProASIC^{PLUS} device in addition to supplying VDD to the FlashPro Lite. The target pc board needs to provide at least 500 mA of current to the FlashPro Lite VDD connection for programming.

3. Silicon Sculptor II and Silicon Sculptor 3 can only provide ISP for ProASIC and ProASIC^{PLUS} families, not for Fusion, IGLOO, or ProASIC3 devices.

Security in Low Power Flash Devices

Security in Action

This section illustrates some applications of the security advantages of Microsemi's devices (Figure 12-6).



Note: Flash blocks are only used in Fusion devices

Figure 12-6 • Security Options

ISP Programming Header Information

The FlashPro4/3/3X programming cable connector can be connected with a 10-pin, 0.1"-pitch programming header. The recommended programming headers are manufactured by AMP (103310-1) and 3M (2510-6002UB). If you have limited board space, you can use a compact programming header manufactured by Samtec (FTSH-105-01-L-D-K). Using this compact programming header, you are required to order an additional header adapter manufactured by Microsemi SoC Products Group (FP3-10PIN-ADAPTER-KIT).

Existing ProASIC^{PLUS} family customers who are using the Samtec Small Programming Header (FTSH-113-01-L-D-K) and are planning to migrate to IGLOO or ProASIC3 devices can also use FP3-10PIN-ADAPTER-KIT.

Manufacturer	Part Number	Description
AMP	103310-1	10-pin, 0.1"-pitch cable header (right-angle PCB mount angle)
3M	2510-6002UB	10-pin, 0.1"-pitch cable header (straight PCB mount angle)
Samtec	FTSH-113-01-L-D-K	Small programming header supported by FlashPro and Silicon Sculptor
Samtec	FTSH-105-01-L-D-K	Compact programming header
Samtec	FFSD-05-D-06.00-01-N	10-pin cable with 50 mil pitch sockets; included in FP3- 10PIN-ADAPTER-KIT.
Microsemi	FP3-10PIN-ADAPTER-KIT	Transition adapter kit to allow FP3 to be connected to a micro 10-pin header (50 mil pitch). Includes a 6 inch Samtec FFSD-05-D-06.00-01-N cable in the kit. The transition adapter board was previously offered as FP3-26PIN-ADAPTER and includes a 26-pin adapter for design transitions from ProASIC ^{PLUS} based boards to ProASIC3 based boards.

Table 13-3 • Programming Header Ordering Codes



Note: *Prog_Mode on FlashPro4 is an output signal that goes High during device programming and returns to Low when programming is complete. This signal can be used to drive a system to provide a 1.5 V programming signal to IGLOO nano, ProASIC3L, and RT ProASIC3 devices that can run with 1.2 V core voltage but require 1.5 V for programming. IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only), but IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

Figure 13-5 • Programming Header (top view)



Note: TCK is correctly wired with an equivalent tie-off resistance of 500Ω , which satisfies the table for VJTAG of 1.5 V. The resistor values for TRST are not appropriate in this case, as the tie-off resistance of 375Ω is below the recommended minimum for VJTAG = 1.5 V, but would be appropriate for a VJTAG setting of 2.5 V or 3.3 V.

Figure 16-3 • Parallel Resistance on JTAG Chain of Devices

Advanced Boundary Scan Register Settings

You will not be able to control the order in which I/Os are released from boundary scan control. Testing has produced cases where, depending on I/O placement and FPGA routing, a 5 ns glitch has been seen on exiting programming mode. The following setting is recommended to prevent such I/O glitches:

- 1. In the FlashPro software, configure the advanced BSR settings for **Specify I/O Settings During Programming**.
- 2. Set the input BSR cell to **Low** for the input I/O.

17 – UJTAG Applications in Microsemi's Low Power Flash Devices

Introduction

In Fusion, IGLOO, and ProASIC3 devices, there is bidirectional access from the JTAG port to the core VersaTiles during normal operation of the device (Figure 17-1). User JTAG (UJTAG) is the ability for the design to use the JTAG ports for access to the device for updates, etc. While regular JTAG is used, the UJTAG tiles, located at the southeast area of the die, are directly connected to the JTAG Test Access Port (TAP) Controller in normal operating mode. As a result, all the functional blocks of the device, such as Clock Conditioning Circuits (CCCs) with PLLs, SRAM blocks, embedded FlashROM, flash memory blocks, and I/O tiles, can be reached via the JTAG ports. The UJTAG functionality is available by instantiating the UJTAG macro directly in the source code of a design. Access to the FPGA core VersaTiles from the JTAG ports enables users to implement different applications using the TAP Controller (JTAG port). This document introduces the UJTAG tile functionality and discusses a few application examples. However, the possible applications are not limited to what is presented in this document. UJTAG can serve different purposes in many designs as an elementary or auxiliary part of the design. For detailed usage information, refer to the "Boundary Scan in Low Power Flash Devices" section on page 357.



Figure 17-1 • Block Diagram of Using UJTAG to Read FlashROM Contents

UJTAG Applications in Microsemi's Low Power Flash Devices

Silicon Testing and Debugging

In many applications, the design needs to be tested, debugged, and verified on real silicon or in the final embedded application. To debug and test the functionality of designs, users may need to monitor some internal logic (or nets) during device operation. The approach of adding design test pins to monitor the critical internal signals has many disadvantages, such as limiting the number of user I/Os. Furthermore, adding external I/Os for test purposes may require additional or dedicated board area for testing and debugging.

The UJTAG tiles of low power flash devices offer a flexible and cost-effective solution for silicon test and debug applications. In this solution, the signals under test are shifted out to the TDO pin of the TAP Controller. The main advantage is that all the test signals are monitored from the TDO pin; no pins or additional board-level resources are required. Figure 17-6 illustrates this technique. Multiple test nets are brought into an internal MUX architecture. The selection of the MUX is done using the contents of the TAP Controller instruction register, where individual instructions (values from 16 to 127) correspond to different signals under test. The selected test signal can be synchronized with the rising or falling edge of TCK (optional) and sent out to UTDO to drive the TDO output of JTAG.

For flash devices, TDO (the output) is configured as low slew and the highest drive strength available in the technology and/or device. Here are some examples:

- 1. If the device is A3P1000 and VCCI is 3.3 V, TDO will be configured as LVTTL 3.3 V output, 24 mA, low slew.
- If the device is AGLN020 and VCCI is 1.8 V, TDO will be configured as LVCMOS 1.8 V output, 4 mA, low slew.
- 3. If the device is AGLE300 and VCCI is 2.5 V, TDO will be configured as LVCMOS 2.5 V output, 24 mA, low slew.

The test and debug procedure is not limited to the example in Figure 17-5 on page 369. Users can customize the debug and test interface to make it appropriate for their applications. For example, multiple test signals can be registered and then sent out through UTDO, each at a different edge of TCK. In other words, *n* signals are sampled with an F_{TCK} / *n* sampling rate. The bandwidth of the information sent out to TDO is always proportional to the frequency of TCK.



Figure 17-6 • UJTAG Usage Example in Test and Debug Applications